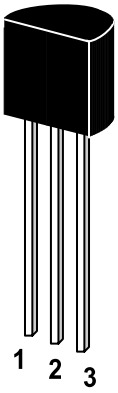
ST 2SA1266

PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Base Current	$-I_B$	50	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_S	-55 to +125	°C

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Characteristics at T_{amb}=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE}$=6V, $-I_C$=2mA					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
G	h_{FE}	200	-	400	-
at $-V_{CE}$=6V, $-I_C$=150mA	h_{FE}	25	-	-	-
Collector Cutoff Current					
at $-V_{CB}$=50V	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current					
at $-V_{EB}$=5V	$-I_{EBO}$	-	-	0.1	μA
Collector Emitter Saturation Voltage					
at $-I_C$=100mA, $-I_B$=10mA	$-V_{CE(sat)}$	-	0.1	0.3	V
Base Emitter Saturation Voltage					
at $-I_C$=100mA, $-I_B$=10mA	$-V_{BE(sat)}$	-	-	1.1	V
Transition Frequency					
at $-V_{CE}$=10V, $-I_E$=1mA	f_T	80	-	-	MHz
Noise Figure					
at $-V_{CE}$=6V, $-I_C$=0.1V, f=1KHZ, R_G=10kΩ	NF	-	1	10	dB
Collector Output Capacitance					
at $-V_{CB}$=10V, f=1MHz	C_{OB}	-	4	7	pF